

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently amended) A voltage-controlled monolithic component of triac type, formed in a substrate ~~(1)~~ of a first conductivity type, including:

a first and a second vertical ~~thyristor (Th1, Th2)~~ thyristors, a first main electrode ~~(A2)~~ of the first thyristor, on a front surface side of the component, corresponding to a first region ~~(6)~~ of ~~(the)~~ a first conductivity type formed in a first well ~~(5)~~ of ~~(the)~~ a second conductivity type, said first well corresponding to a first main electrode ~~(A2)~~ of the second thyristor, the first well containing a second region ~~(8)~~ of the first conductivity type; and

a pilot structure including, on the front surface side, above an extension of a second main electrode region ~~(4)~~ of the second thyristor, a second well ~~(11)~~ of the second conductivity type containing third and fourth regions of the first conductivity type, the third region ~~(12)~~ and a portion of the second well ~~(11)~~ being connected to a gate terminal ~~(G)~~, the fourth region ~~(13)~~ being connected to the second region ~~(8)~~.

2. (Currently amended) The component of claim 1, wherein the component is surrounded at its periphery with a wall of the second conductivity type ~~(2)~~ extending from one surface to the other of the component.

3. (Currently amended) The component of claim 2, wherein, on the front surface side, the first well ~~(5)~~ includes an extension ~~(16)~~ which surrounds the second well ~~(11)~~.

4. (Currently amended) The component of claim 3, wherein an external periphery of the first well and of its extension is surrounded with a lightly-doped ring ~~(17)~~ of the second conductivity type.